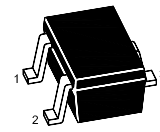
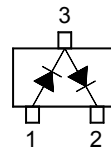


BAV99W

Silicon Epitaxial Planar Switching Diode



SOT-323 Plastic Package

Marking Code: A7

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	100	V
Continuous Forward Current Single Diode Load Double Diode Load	I_F	150 130	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current at $t = 1\ \mu\text{s}$ at $t = 1\ \text{ms}$ at $t = 1\ \text{s}$	I_{FSM}	4 1 0.5	A
Total Power Dissipation	P_{tot}	200	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 10\ \text{mA}$ at $I_F = 50\ \text{mA}$ at $I_F = 150\ \text{mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25\ \text{V}$ at $V_R = 80\ \text{V}$ at $V_R = 25\ \text{V}$, $T_j = 150^\circ\text{C}$ at $V_R = 80\ \text{V}$, $T_j = 150^\circ\text{C}$	I_R	30 0.5 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0$, $f = 1\ \text{MHz}$	C_d	1.5	pF
Reverse Recovery Time at $I_F = 10\ \text{mA}$, $I_R = 60\ \text{mA}$, $I_{rr} = 0.1 \times I_R$	t_{rr}	4	ns

